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# N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (A)		
150	0.017 at V <sub>GS</sub> = 10 V	75		
	$0.022 \text{ at V}_{GS} = 4.5 \text{ V}$	60		

#### **FEATURES**

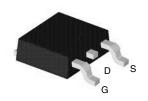
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> Tested



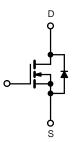
#### **APPLICATIONS**

· Primary Side Switch

# TO-252 Pin Configuration



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	150	V		
Gate-Source Voltage		V <sub>GS</sub>	± 20	7 v		
Continuous Proin Current /T 475 °C\b	T <sub>C</sub> = 25 °C	I-	75			
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 125 °C	l <sub>D</sub>	52.2			
Pulsed Drain Current	I <sub>DM</sub>	175	Α			
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	75				
Avalanche Current	I <sub>AR</sub>	39				
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AR</sub>	195	mJ		
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	189 <sup>b</sup>	W		
Maximum Fower Dissipation	T <sub>A</sub> = 25 °C	' b	8.5 <sup>a</sup>	VV		
Operating Junction and Storage Temperature Range	•	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
hungtion to Ambienta	t ≤ 10 s	- R <sub>thJA</sub>	15	20	°C/W	
Junction-to-Ambient <sup>a</sup>	Steady State		42	53		
Junction-to-Case		R <sub>thJC</sub>	0.5	0.9		

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static					l		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.2		3.0		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	$I_{DSS}$	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	50		μΑ		
		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	7	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	75			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		0.017	17		
5 1 2 2 2 2 1 5 1 b	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C		0.023		Ω	
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C		0.028			
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A		0.022			
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		52		S	
Dynamic <sup>a</sup>							
Input Capacitance	C <sub>iss</sub>			2420		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		155			
Reverse Transfer Capacitance	C <sub>rss</sub>			10			
Total Gate Charge <sup>c</sup>	$Q_g$			28	38		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		5.5		nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			5			
Gate Resistance	$R_g$		1		3.2	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			9	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 75 \text{ V}, R_L = 5 \Omega$		10	15	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5$		25	45		
Fall Time <sup>c</sup>	t <sub>f</sub>	Ω		10	24		
Source-Drain Diode Ratings and Char	racteristic (T	<sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				175	Α	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, dl/dt = 100 A/μs		85	99	ns	

#### Notes:

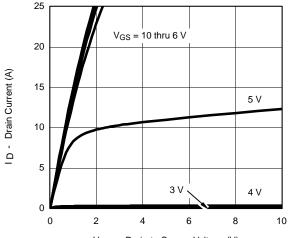
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

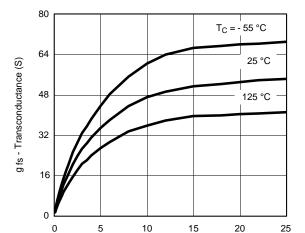




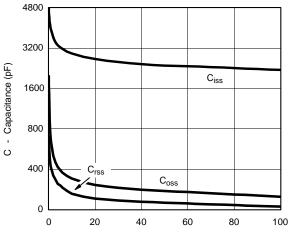
### TYPICAL CHARACTERISTICS (25 °C unless noted)



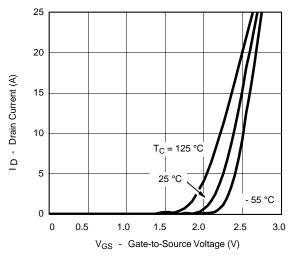
 $V_{DS}\,$  - Drain-to-Source Voltage (V) **Output Characteristics** 



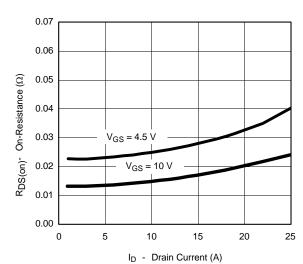
I<sub>D</sub> - Drain Current (A) **Transconductance** 



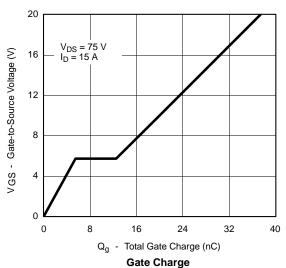
 $V_{DS}\,$  - Drain-to-Source Voltage (V) Capacitance



**Transfer Characteristics** 



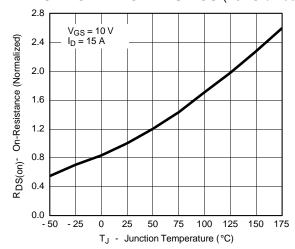
On-Resistance vs. Drain Current





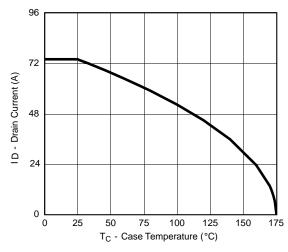
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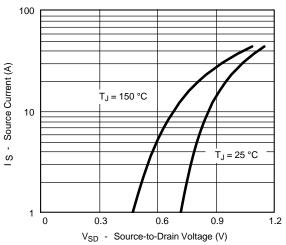


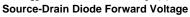
On-Resistance vs. Junction Temperature

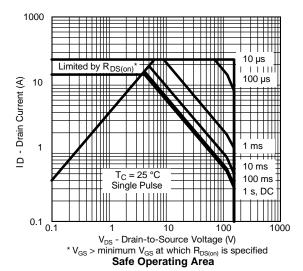
#### THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



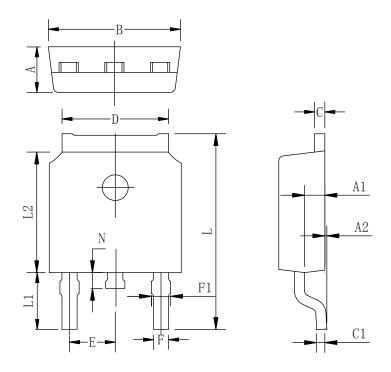




Normalized Thermal Transient Impedance, Junction-to-Case

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# TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
С	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	





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